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Plasma enhanced atomic layer deposition of zinc sulfide thin films

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Zinc sulfide thin films were deposited by plasma enhanced atomic layer deposition (PE-ALD) using diethylzinc and H₂S/Ar plasma. The growth characteristics were studied in situ with spectroscopic ellipsometry and ex situ with x-ray reflectometry. The growth was linear and self-limited. Furthermore, it was demonstrated that the growth per cycle was less temperature dependent for the PE-ALD process compared to the thermal process. ZnS thin film properties were investigated ex situ using x-ray photoelectron spectroscopy, x-ray diffraction, ultraviolet/visible optical spectroscopy, and atomic force microscopy. The as-deposited films were crystalline with a transmittance of >90% and a band gap of 3.49 eV. ZnS films deposited by PE-ALD were smoother than films deposited by thermal ALD. The plasma enhanced ALD process may have an advantage for ALD of ternary compounds where different temperature windows have to be matched or for applications where a smooth interface is required. © 2016 American Vacuum Society.

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I. INTRODUCTION

Zinc sulfide is a nontoxic wide band gap II–VI semiconductor which can be doped n- and p-type. Two main crystalline forms exist: the cubic zinc blend structure and the hexagonal wurtzite. The main applications for zinc sulfide are as luminescent host material in, e.g., thin film electroluminescent displays, and as optical windows or coatings in the near infrared region. Recently, ZnS attracted much attention for its application as a Cd-free buffer layer in CIGS thin film solar cells, and as optical windows or coatings in the near infrared. ZnS is a p-type transparent conductor widely used in devices such as field effect transistors. Atomic layer deposition (ALD) is an ideal deposition technique for these applications since they require a high degree of control over the layer thickness as well as conformal layers.

ALD is a self-limited deposition method that is characterized by alternating exposure of the growing film to different chemical precursors, resulting in the sequential deposition of (sub)monolayers over the exposed sample surface. The self-limiting nature of the vapor–solid reactions ensures pinhole free inorganic coatings with a precise thickness controlled at the atomic scale and a superb conformity onto large scale substrates with complex topologies.

The first ZnS ALD processes reported in the 1970s used elemental zinc and sulfur as precursors. These processes require high source temperatures and therefore high deposition temperatures of 500 °C which limits the potential applications. Shortly after, the atomic precursors were substituted for molecular ones such as H₂S and halides like ZnCl₂ (Refs. 10–12) or ZnI₂. Although having already lower deposition temperatures of around 300–400 °C, these temperatures are still too high for some applications. Furthermore, halide precursors have the disadvantage that they leave impurities in the ZnS films. Therefore, metalorganic precursors such as diethylzinc (DEZ) and dimethylzinc were started to be investigated as an alternative. These precursors typically have a wide temperature stability and a high vapor pressure resulting in a large temperature range and high growth per cycle (GPC), respectively. However, using the thermal DEZ and H₂S process, a monotonically decreasing GPC is observed with increasing temperature.

Apart from H₂S and elemental S, only a few alternatives for the S source in ZnS ALD were investigated. One promising approach is the in situ production of H₂S from thioacetamide. In this study, we report a novel plasma enhanced ALD process for ZnS using DEZ and an argon diluted hydrogen sulfide plasma [(H₂S/Ar)*] as an alternative S source. In comparison to the thermal DEZ and H₂S process, this new process showed less temperature sensitivity, and a high GPC was obtained for temperatures up to 300 °C. The structural and optical properties of plasma enhanced atomic layer deposition (PE-ALD) ZnS were compared to thermal ALD ZnS.

II. EXPERIMENTAL DETAILS

Zinc sulfide thin films were deposited in a home-built pump-type ALD reactor by using DEZ (>95%, Strem Chemicals) in combination with H₂S/Ar plasma as reactants. The DEZ precursor was stored in a stainless steel bottle at room temperature while the DEZ precursor line was heated to 50 °C. The substrates were Si(100) wafers covered with 100 nm thermally grown SiO₂ or quartz for optical transmission measurements. To estimate the conformity of the process,
SiO2 covered micropillars were used as a substrate. Argon diluted H2S plasma was used instead of pure H2S plasma in order to minimize the exposure of the ALD reactor to the highly reactive S radicals. The plasma was generated remotely from the substrate by radio frequency inductive coupling at 200 W. The substrate temperature was varied from 60 to 300 °C. A standard ALD cycle consisted of 5 s precursor pulses followed by 25 s of pumping.

The ZnS thin film growth rate was monitored in situ by spectroscopic ellipsometry (SE) using a library model based on an oscillator model. This model was verified by measuring several ZnS thin films ex situ with x-ray reflectivity (XRR) and comparing the obtained film thickness with the SE measurements. Even during the first cycles of the film growth, good quality fits to the ellipsometric data were obtained.

X-ray photoelectron spectroscopy (XPS) was used to determine the chemical composition of the deposited ZnS films. All measurements were performed in-house with a Theta Probe system from Thermo Scientific using Al Kα x-rays generated at 15 kV and focused to a spot size of 0.3 mm by an MXR1 monochromator gun. In order to remove surface contamination, the samples were etched with Ar+ ions at an acceleration voltage of 3 keV and a current of 2 μA. The obtained binding energies (BE) were calibrated by using a BE of 284.6 eV for the carbon peak.

X-ray diffraction (XRD) and x-ray reflectivity (XRR) patterns were obtained with a Bruker D8 Discover using a Cu Kα x-ray source and a linear detector.

The optical properties of ZnS were measured in the UV/Vis range with a spectrophotometer (Perkin Elmer Lambda 950) on quartz substrates. Transmittance spectra were measured in the range of 250–1000 nm. The measured transmittance was divided by the transmittance of the bare quartz substrate in order to obtain only the transmittance of the ZnS film.

Scanning electron microscopy (SEM) and energy-dispersive x-ray spectroscopy (EDX) measurements were performed in an FEI SEM at an energy of 12 keV and a silicon-drift detector was used.

The surface morphology of the films was determined by atomic force microscopy (AFM) on a Bruker Dimension Edge system operating in tapping mode in air. The root mean square (RMS) roughness was calculated from 3 × 3 μm scans.

The plasma enhanced process was characterized using optical emission spectroscopy and mass spectrometer analysis. An Ocean Optics QE Pro spectrometer coupled to the plasma column (soda-lime glass) by an optical fiber was used to obtain optical emission spectra. Mass spectrometry was carried out in situ during the ALD process with a HPR-30 mass spectrometer from Hiden.

III. RESULTS AND DISCUSSION

A. ALD growth characterization

The linearity and growth characteristics of the thermal ALD and PE-ALD ZnS processes were studied at 65 and 150 °C on Si substrates covered with 100 nm thermally grown SiO2. The ZnS film thickness was calculated from in situ spectral ellipsometry measurements performed after completed ALD cycles. This is displayed as a function of ALD cycles in Fig. 1. For both processes, the growth was linear after a short nucleation time. It can be seen that the H2S/Ar plasma enhanced process nucleated slightly earlier than the thermal process. As opposed to the thermal ALD process, the PE-ALD process showed only a minor dependency on the deposition temperature.

The ALD windows of the thermal and PE-ALD ZnS processes were determined by measuring the GPC with in situ spectroscopic ellipsometry for different substrate temperatures from 65 to 300 °C (Fig. 2). The thermal and PE-ALD processes had the same maximal GPC of 1.7 Å/cycle at a temperature of 65 °C which corresponds to a growth rate of approximately 0.5 monolayers/cycle using the lattice dimension of 3.12 Å for the cubic [111] growth direction. The thermal processes showed a decrease in GPC for increasing...
deposition temperature of more than 70% over the investigated temperature range which is in accordance to the earlier reports.\textsuperscript{15–18} In contrast, only a minor temperature dependency for the PE-ALD process was found. The GPC of the PE-ALD process dropped by 20% for a deposition temperature of 250°C. At higher temperatures, the GPC started to rise again. This may be related to the self-decomposition of the DEZ precursor, although this should normally only start at around 320°C.\textsuperscript{20} The increased GPC of the PE-ALD process in comparison with the thermal one can lead to a better device integration or better matching of temperature windows for ALD of ternary compounds.\textsuperscript{21,22}

The saturation behavior of the PE-ALD process was studied at a temperature of 65 and 150°C by measuring the GPC with \textit{in situ} spectroscopic ellipsometry while varying the pulse time of the precursors and reactants. Figure 3 shows the GPC as a function of the pulse time of DEZ and (H\textsubscript{2}S/Ar)* for a deposition temperature of (a) 65°C and (b) 150°C. The PE-ALD process at 65°C saturates after approximately 3 s while the PE-ALD at 150°C saturates after approximately 4–5 s.

Optical emission spectroscopy was used to obtain an overview over the reactive species present in the PE-ALD process. Figure 4(a) shows the optical emission spectrum of the H\textsubscript{2}S/Ar plasma. Since all the features related to the H\textsubscript{2}S disappeared in the high intensity Ar spectrum, a pure H\textsubscript{2}S plasma was investigated [Fig. 4(b)]. The spectrum contained a molecular band with various peaks in the wavelength range from 370 to 475 nm. This band was related to H\textsubscript{2}S\textsuperscript{+}.\textsuperscript{23,24} Furthermore, the spectrum contained hydrogen revealed by the H-\textalpha{} and H-\textbeta{} peak from the Balmer series at 656.3 and 486.1 nm, respectively. Finally, the spectrum showed indications of S with peaks around 660–730 nm which were identified with S\textsuperscript{1+}.\textsuperscript{25–27}

It is known that elemental sulfur exists in various allotropes and that a H\textsubscript{2}S or H\textsubscript{2}S/Ar plasma can form a large variety of sulfur–hydrogen species S\textsubscript{x}H\textsubscript{y} with x up to 11 and y = 0 to 5.\textsuperscript{28–30} Therefore, it is most likely that these species were also formed during our ALD process. Previous research on H\textsubscript{2}S or H\textsubscript{2}S/Ar plasma showed that S\textsubscript{2} can be detected at 260 nm in the optical emission spectrum\textsuperscript{28} and that S\textsubscript{x}H\textsubscript{y} species with x > 2 can be detected with mass spectrometry.\textsuperscript{30} In our setup, the detection of the S\textsubscript{2} peak in the optical emission spectrum was not possible due to the use of a plasma column made out of soda-lime glass instead of quartz glass. The used glass absorbed light below 300 nm did not allow for the detection of the S\textsubscript{2} peak at 260 nm.

Finally, \textit{in situ} mass spectrometry measurements were used to investigate the H\textsubscript{2}S/Ar plasma. In contrast to the results reported in the work of Ellmer, no S\textsubscript{x}H\textsubscript{y} species with x > 1 were found during our measurements. An explanation for this may be that Ellmer collected and analyzed the ions coming directly from the plasma (direct line-of-sight) without any further ionization while our mass spectrometer was not in direct line-of-sight to the plasma. Furthermore, in our mass spectrometer, the ions from the plasma were first broken down by electron impact ionization and then analyzed. Therefore, all S\textsubscript{x}H\textsubscript{y} species with x > 1 which may have been formed in the plasma were most likely broken down into...
fragments in the mass spectrometer. In order to get more insights into the reaction mechanism of the PE-ALD ZnS process, in situ mass spectrometry measurements were done during a sequence of thermal and PE-ALD ZnS cycles. Since the partial pressure of Ar in the H2S/Ar plasma was too high to detect any reaction products, a pure H2S plasma was used. Figure 5(a) shows the schematic diagram of the investigated ALD cycles. Three PE-ALD cycles were followed by three cycles of thermal ALD. Multiple ion detection mass spectrometry measurements were used to follow the evolution of specific mass-to-charge ratio (m/z) signals during these ALD cycles. The following precursors and potential reaction species were monitored: H2S at m/z = 34, CS2 at m/z = 76, CS at m/z = 44, and fragments of ethane (C2H6) at m/z = 28. Figure 5(b) shows the partial pressure of the H2S signal. It can be seen that the signal of H2S coincided with the pulses of either H2S/Ar plasma or H2S. Figure 5(c) shows the partial pressure of ions and molecules at m/z = 28. This signal may originate either from fragments of DEZ (as it coincided with DEZ pulses) or from fragments of ethane, which is a reaction product of both half reactions in the thermal DEZ and H2S ALD process. This signal was found during both types of processes suggesting that ligand exchange reactions are also taking place during PE-ALD. CS2 and CS are reaction products of a combustion-type reaction between DEZ and H2S. While no CS signal was detected, some CS2 was detected at a partial pressure of 10^-8 Torr which is 2 orders of magnitude lower than H2S and the ethane fragments [Fig. 5(d)]. However, it was only detected during the PE-ALD pulses and not during the thermal ALD. The presence of CS2 during the PE-ALD cycle may suggest that the PE-ALD process had some contribution of a combustion-type reaction.

B. Material properties

The material properties of ZnS deposited by PE-ALD were compared against the material properties of ZnS deposited with thermal ALD. Based on the results found during the ALD growth characterization, the main focus was put on intermediate deposition temperatures of approximately 150 °C. In this region, the PE-ALD process has a potential advantage over the thermal process, as it offers a higher GPC.

XPS measurements were used to check the ZnS films for impurities. Figure 6 shows the XPS analysis of ZnS deposited by PE-ALD at 65 and 150 °C. The two upper survey spectra represent PE-ALD ZnS deposited at 150 °C while the two lower represent PE-ALD ZnS deposited at 65 °C. It can be seen that the surface was oxidized and contaminated with carbon for both temperatures. After sputtering away some of the surface material, the oxygen and carbon content of the ZnS film was below the detection limit of approximately 1%, indicating that a pure film without contamination was obtained. The Zn to S ratio was determined from the XPS spectra. Near-stoichiometric atomic ratios of 56:44 and 53:47 were found for the samples deposited at 65 and 150 °C, respectively. No excess of sulfur for lower temperature was found, showing that no condensation of sulfur occurred.

The crystallinity of ZnS thin films was investigated with XRD. Figure 7 shows the XRD pattern of the as-deposited 60 nm thick ZnS films deposited by thermal and PE-ALD at 80 °C. Both the thermal and PE-ALD ZnS films were already crystalline as deposited with mainly the zincblende phase growing along the [111] plane. Based on the full width half max of the main peak at 28.6°, it was estimated that ZnS

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**Fig. 5.** (Color online) (a) Schematic diagram of the process sequences used during mass spectrometry. Partial pressure of (b) the H2S signal at m/z = 34, (c) the signal from fragments of ethane at m/z = 28, and (d) the CS2 signal at m/z = 76 derived from multiple ion detection mass spectrometry measurements during a sequence of thermal and PE-ALD ZnS cycles.

**Fig. 6.** (Color online) XPS survey spectra of PE-ALD ZnS deposited at 65 and 150 °C before and after sputtering.
thin films deposited by PE-ALD had smaller grain sizes than ZnS films deposited with thermal ALD.

The optical properties of the as-deposited ZnS films were determined using optical transmittance measurements. An 11 nm (PE-ALD) and 15 nm (thermal ALD) thick ZnS film were deposited on a quartz substrate at 150 °C. The transmittance of these films is shown in the inset of Fig. 8. The films had an optical transmission of nearly 100% in the visible region, which is an important property for applications of ZnS as a TCL material or as an antireflective coating. To determine the band gap (E_g) of the material, a Tauc-plot was used, where \( a(h\nu)^2 \) was plotted versus the photon energy (Fig. 8). The absorption coefficient \( a \) was calculated from the transmittance \( T \) and the film thickness \( d \), as
\[
a = \frac{\ln(T)}{d}.
\] Since ZnS has a direct band gap, it can be determined from the Tauc-plot by interpolation of the fit of the linear part of the absorption edge to zero. For the PE-ALD and thermal process, a band gap of 3.49 and 3.53 eV, respectively, was found. These values agree with the values reported in literature.

The conformality of the ZnS coating on nonplanar substrates was studied by coating Si micropillars with 10 nm ZnS grown using thermal and PE-ALD. These Si micropillars had a width of 2 μm, height of 50 μm, and a center-to-center spacing of 4 μm. ALD was done at 150 °C using optimized deposition parameters with doubled precursor pulse times and purging times. Cross sections of these samples were investigated with SEM and EDX. Figure 9(b) shows the SEM cross section of micropillars coated with 10 nm PE-ALD ZnS. Since no contrast between the ZnS and Si was observed, various EDX line scans were performed at different positions along the micropillars [indicated by the vertical lines in Fig. 9(b)]. The total amount of deposited ZnS was estimated from the EDX scans [Fig. 9(a)] by integrating over the Zn L peak. Figure 9(c) compares the amount of Zn at different depths along the pillars for samples coated with thermal and PE-ALD. Even at the bottom of the micropillars, more than 90% Zn was found in comparison to the reference on top of the micropillars. By further optimizing the pulse and purge duration of each precursor, a conformal coating of larger aspect ratios should be possible.

AFM was used to study the morphology of ZnS films with increasing thickness from 10 to 36 nm. From the AFM
images, the RMS roughness was measured on area scans of $3 \times 3 \mu m$. Figure 10 shows the AFM image of 20 nm thick ZnS films deposited at 150 °C by (a) thermal ALD and (b) PE-ALD. It can be seen that ZnS thin films deposited by PE-ALD had a smoother surface than ZnS films deposited by thermal ALD. This may be explained by a smaller average grain size in ZnS films deposited by PE-ALD as indicated by XRD measurements. Figure 10(c) shows the RMS roughness as a function of the ZnS layer thickness. The thermal ALD process shows an increase in the RMS roughness for thicker ZnS layers which was already reported in previous works.16,20,34 The same trend was observed for the PE-ALD. For applications where a smooth ZnS interface is important such as CIGS solar cells,35 PE-ALD ZnS may have an advantage over thermal ALD ZnS.

IV. CONCLUSIONS

A new plasma enhanced ALD ZnS process was developed using DEZ and H$_2$S/Ar plasma. This process had a deposition window which was less temperature dependent than the deposition window of the thermal process which may lead to a better device integration or better matching of temperature windows for ALD of ternary compounds. ZnS films deposited by PE-ALD had similar optical and structural properties as ZnS thin films deposited by thermal ALD which was confirmed by XPS, XRD, and UV/Vis measurements. XPS studies confirmed the growth of ZnS without any detectable O or C contaminations. XRD revealed that the as-deposited films were already crystalline, making further annealing unnecessary. PE-ALD ZnS films showed a transmittance of more than 90% over the visible range, and the band gap was determined to be 3.49 eV. Conformal growth on micropillars was demonstrated. Finally, it was observed that ZnS deposited by PE-ALD has smoother surfaces in comparison to thermal ALD making this process potentially more attractive for solar cell application where a smooth interface is needed.

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